

74LVC3G07

Triple buffer with open-drain output

Rev. 03 — 01 February 2005

Product data sheet

1. General description

The 74LVC3G07 is a high-performance, low-power, low-voltage, Si-gate CMOS device and superior to most advanced CMOS compatible TTL families.

Input can be driven from either 3.3 V or 5 V devices. This feature allows the use of this device in a mixed 3.3 V and 5 V environment.

Schmitt trigger action at all inputs makes the circuit tolerant for slower input rise and fall time.

This device is fully specified for partial power-down applications using I_{off} . The I_{off} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

The 74LVC3G07 provides three non-inverting buffers.

The output of the device is an open drain and can be connected to other open-drain outputs to implement active-LOW wired-OR or active-HIGH wired-AND functions.

2. Features

- Wide supply voltage range from 1.65 V to 5.5 V
- 5 V tolerant input/output for interfacing with 5 V logic
- High noise immunity
- Complies with JEDEC standard:
 - ◆ JESD8-7 (1.65 V to 1.95 V)
 - ◆ JESD8-5 (2.3 V to 2.7 V)
 - ◆ JESD8-B/JESD36 (2.7 V to 3.6 V).
- ESD protection:
 - ◆ HBM EIA/JESD22-A114-B exceeds 2000 V
 - ◆ MM EIA/JESD22-A115-A exceeds 200 V.
- -24 mA output drive ($V_{CC} = 3.0$ V)
- CMOS low power consumption
- Latch-up performance exceeds 250 mA
- Direct interface with TTL levels
- Inputs accept voltages up to 5 V
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C.

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3. Quick reference data

Table 1: Quick reference data

$GND = 0\text{ V}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
t_{PLZ} , t_{PZL}	propagation delay input nA to output nY	$V_{CC} = 1.8\text{ V}$; $C_L = 30\text{ pF}$; $R_L = 1\text{ k}\Omega$	-	2.9	-	ns
		$V_{CC} = 2.5\text{ V}$; $C_L = 30\text{ pF}$; $R_L = 500\text{ }\Omega$	-	1.7	-	ns
		$V_{CC} = 2.7\text{ V}$; $C_L = 50\text{ pF}$; $R_L = 500\text{ }\Omega$	-	2.3	-	ns
		$V_{CC} = 3.3\text{ V}$; $C_L = 50\text{ pF}$; $R_L = 500\text{ }\Omega$	-	2.1	-	ns
		$V_{CC} = 5.0\text{ V}$; $C_L = 50\text{ pF}$; $R_L = 500\text{ }\Omega$	-	1.5	-	ns
C_I	input capacitance		-	2.5	-	pF
C_{PD}	power dissipation capacitance per gate	$V_{CC} = 3.3\text{ V}$	[1] [2]	6.5	-	pF

[1] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:

f_i = input frequency in MHz;

f_o = output frequency in MHz;

C_L = output load capacitance in pF;

V_{CC} = supply voltage in Volts;

N = number of inputs switching;

$\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

[2] The condition is $V_I = GND$ to V_{CC} .

4. Ordering information

Table 2: Ordering information

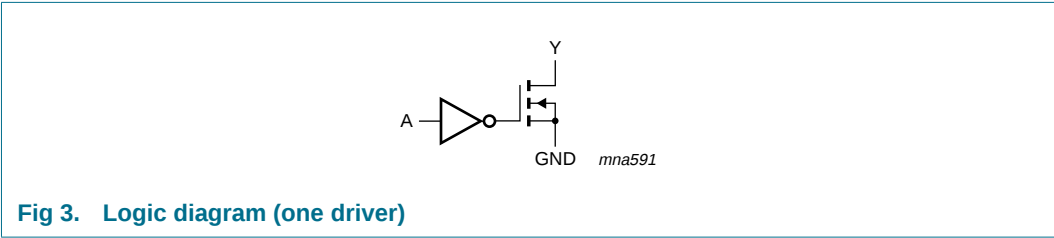
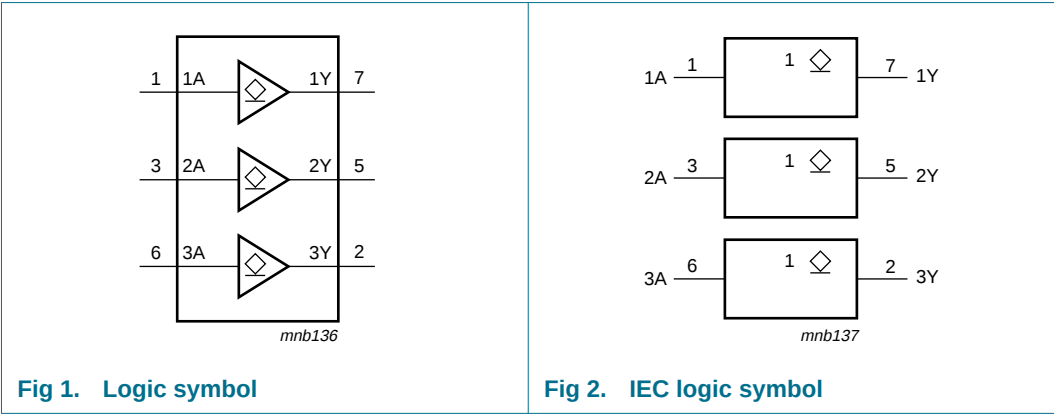
Type number	Package			
	Temperature range	Name	Description	Version
74LVC3G07DP	-40 °C to +125 °C	TSSOP8	plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm	SOT505-2
74LVC3G07DC	-40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1
74LVC3G07GT	-40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body $1 \times 1.95 \times 0.5\text{ mm}$	SOT833-1

5. Marking

Table 3: Marking codes

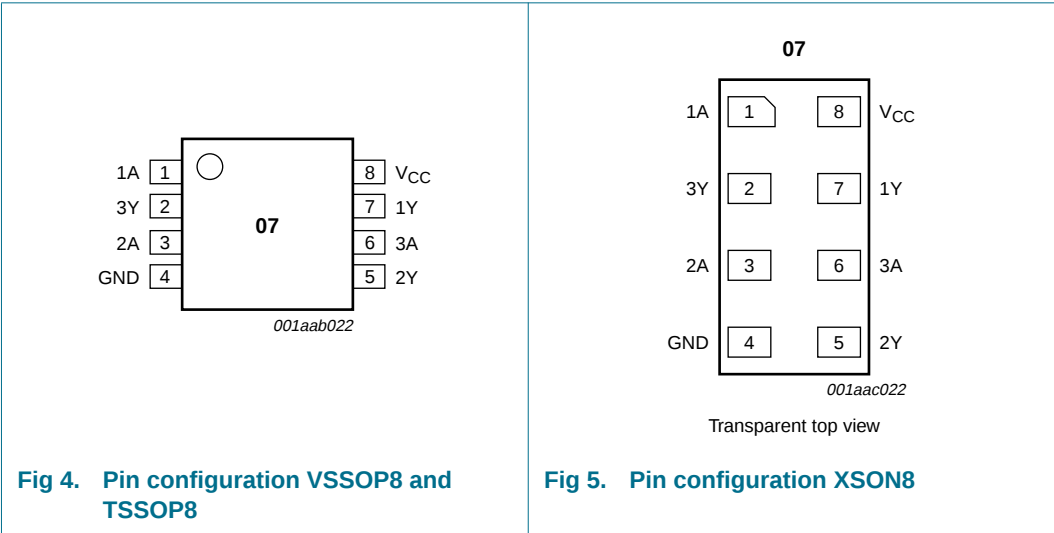
Type number	Marking code
74LVC3G07DP	V07
74LVC3G07DC	V07
74LVC3G07GT	V07

6. Functional diagram



7. Pinning information

7.1 Pinning



7.2 Pin description

Table 4: Pin description

Symbol	Pin	Description
1A	1	data input
3Y	2	data output
2A	3	data input
GND	4	ground (0 V)
2Y	5	data output
3A	6	data input
1Y	7	data output
V _{CC}	8	supply voltage

8. Functional description

8.1 Function table

Table 5: Function table ^[1]

Input nA	Output nY
L	L
H	Z

- [1] H = HIGH voltage level;
 L = LOW voltage level;
 Z = high-impedance OFF-state.

9. Limiting values

Table 6: Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+6.5	V
V _I	input voltage		^[1] -0.5	+6.5	V
V _O	output voltage	active mode	^[1] -0.5	+6.5	V
		Power-down mode	^{[1] [2]} -0.5	+6.5	V
I _{IK}	input diode current	V _I < 0 V	-	-50	mA
I _{OK}	output diode current	V _O < 0 V	-	-50	mA
I _O	output sink current	V _O = 0 V to 6.5 V	-	50	mA
I _{CC} , I _{GND}	V _{CC} or GND current		-	±100	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	power dissipation	T _{amb} = -40 °C to +125 °C	-	300	mW

- [1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
 [2] When V_{CC} = 0 V (Power-down mode), the output voltage can be 5.5 V in normal operation.

10. Recommended operating conditions

Table 7: Recommended operating conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CC}	supply voltage		1.65	-	5.5	V
V_I	input voltage		0	-	5.5	V
V_O	output voltage	active mode	0	-	V_{CC}	V
		Power-down mode; $V_{CC} = 0$ V	0	-	5.5	V
T_{amb}	ambient temperature		-40	-	+125	°C
t_r, t_f	input rise and fall times	$V_{CC} = 1.65$ V to 2.7 V	0	-	20	ns/V
		$V_{CC} = 2.7$ V to 5.5 V	0	-	10	ns/V

11. Static characteristics

Table 8: Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$T_{amb} = -40$ °C to +85 °C [1]						
V_{IH}	HIGH-level input voltage	$V_{CC} = 1.65$ V to 1.95 V	$0.65 \times V_{CC}$	-	-	V
		$V_{CC} = 2.3$ V to 2.7 V	1.7	-	-	V
		$V_{CC} = 2.7$ V to 3.6 V	2.0	-	-	V
		$V_{CC} = 4.5$ V to 5.5 V	$0.7 \times V_{CC}$	-	-	V
V_{IL}	LOW-level input voltage	$V_{CC} = 1.65$ V to 1.95 V	-	-	$0.35 \times V_{CC}$	V
		$V_{CC} = 2.3$ V to 2.7 V	-	-	0.7	V
		$V_{CC} = 2.7$ V to 3.6 V	-	-	0.8	V
		$V_{CC} = 4.5$ V to 5.5 V	-	-	$0.3 \times V_{CC}$	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = 100$ μ A; $V_{CC} = 1.65$ V to 5.5 V	-	-	0.1	V
		$I_O = 4$ mA; $V_{CC} = 1.65$ V	-	-	0.45	V
		$I_O = 8$ mA; $V_{CC} = 2.3$ V	-	-	0.3	V
		$I_O = 12$ mA; $V_{CC} = 2.7$ V	-	-	0.4	V
		$I_O = 24$ mA; $V_{CC} = 3.0$ V	-	-	0.55	V
		$I_O = 32$ mA; $V_{CC} = 4.5$ V	-	-	0.55	V
I_{LI}	input leakage current	$V_I = 5.5$ V or GND; $V_{CC} = 1.65$ V to 5.5 V	-	± 0.1	± 5	μ A
I_{OZ}	3-state output OFF-state current	$V_I = V_{IH}$ or V_{IL} ; $V_O = V_{CC}$ or GND; $V_{CC} = 5.5$ V	-	± 0.1	± 10	μ A
I_{off}	power-off leakage current	V_I or $V_O = 5.5$ V; $V_{CC} = 0$ V	-	± 0.1	± 10	μ A
I_{CC}	quiescent supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5$ V	-	0.1	10	μ A
ΔI_{CC}	additional quiescent supply current per pin	$V_I = V_{CC} - 0.6$ V; $I_O = 0$ A; $V_{CC} = 2.3$ V to 5.5 V	-	5	500	μ A
C_I	input capacitance		-	2.5	-	pF

Table 8: Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
T_{amb} = -40 °C to +125 °C						
V _{IH}	HIGH-level input voltage	V _{CC} = 1.65 V to 1.95 V	0.65 × V _{CC}	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.7	-	-	V
		V _{CC} = 2.7 V to 3.6 V	2.0	-	-	V
		V _{CC} = 4.5 V to 5.5 V	0.7 × V _{CC}	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 1.65 V to 1.95 V	-	-	0.35 × V _{CC}	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V _{CC} = 2.7 V to 3.6 V	-	-	0.8	V
		V _{CC} = 4.5 V to 5.5 V	-	-	0.3 × V _{CC}	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = 100 µA; V _{CC} = 1.65 V to 5.5 V	-	-	0.1	V
		I _O = 4 mA; V _{CC} = 1.65 V	-	-	0.70	V
		I _O = 8 mA; V _{CC} = 2.3 V	-	-	0.45	V
		I _O = 12 mA; V _{CC} = 2.7 V	-	-	0.60	V
		I _O = 24 mA; V _{CC} = 3.0 V	-	-	0.80	V
		I _O = 32 mA; V _{CC} = 4.5 V	-	-	0.80	V
I _{LI}	input leakage current	V _I = 5.5 V or GND; V _{CC} = 1.65 V to 5.5 V	-	-	±20	µA
I _{OZ}	3-state output OFF-state current	V _I = V _{IH} or V _{IL} ; V _O = V _{CC} or GND; V _{CC} = 5.5 V	-	-	±10	µA
I _{off}	power-off leakage current	V _I or V _O = 5.5 V; V _{CC} = 0 V	-	-	±20	µA
I _{CC}	quiescent supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 5.5 V	-	-	40	µA
ΔI _{CC}	additional quiescent supply current per pin	V _I = V _{CC} - 0.6 V; I _O = 0 A; V _{CC} = 2.3 V to 5.5 V	-	-	5000	µA

[1] All typical values are measured at nominal V_{CC} and T_{amb} = 25 °C.

12. Dynamic characteristics

Table 9: Dynamic characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
T_{amb} = -40 °C to +85 °C [1]						
t _{PLZ} , t _{PZL}	propagation delay input nA to output nY	see Figure 6 and 7				
		V _{CC} = 1.65 V to 1.95 V	1.0	2.9	6.7	ns
		V _{CC} = 2.3 V to 2.7 V	0.5	1.7	4.3	ns
		V _{CC} = 2.7 V	1.0	2.3	4.2	ns
		V _{CC} = 3.0 V to 3.6 V	0.5	2.1	3.7	ns
		V _{CC} = 4.5 V to 5.5 V	0.5	1.5	2.9	ns

Table 9: Dynamic characteristics ...continued
At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
C _{PD}	power dissipation capacitance per gate	V _{CC} = 3.3 V	[2] [3] -	6.5	-	pF
T _{amb} = -40 °C to +125 °C						
t _{PLZ} , t _{PZL}	propagation delay input nA to output nY	see Figure 6 and 7				
		V _{CC} = 1.65 V to 1.95 V	1.0	-	8.4	ns
		V _{CC} = 2.3 V to 2.7 V	0.5	-	5.5	ns
		V _{CC} = 2.7 V	1.0	-	5.3	ns
		V _{CC} = 3.0 V to 3.6 V	0.5	-	4.7	ns
		V _{CC} = 4.5 V to 5.5 V	0.5	-	3.7	ns

- [1] All typical values are measured at nominal V_{CC} and T_{amb} = 25 °C.
- [2] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).
P_D = C_{PD} × V_{CC}² × f_i × N + Σ(C_L × V_{CC}² × f_o) where:
f_i = input frequency in MHz;
f_o = output frequency in MHz;
C_L = output load capacitance in pF;
V_{CC} = supply voltage in Volts;
N = number of inputs switching;
Σ(C_L × V_{CC}² × f_o) = sum of outputs.
- [3] The condition is V_I = GND to V_{CC}.

13. Waveforms

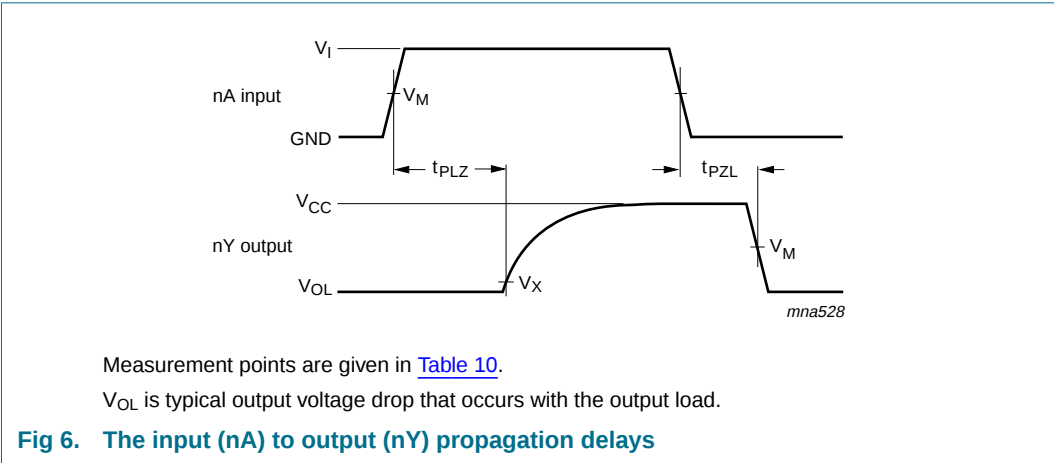


Table 10: Measurement points

Supply voltage	Input		Output	
V _{CC}	V _M	V _I	V _M	V _X
1.65 V to 1.95 V	0.5 × V _{CC}	V _{CC}	0.5 × V _{CC}	V _{OL} + 0.15 V
2.3 V to 2.7 V	0.5 × V _{CC}	V _{CC}	0.5 × V _{CC}	V _{OL} + 0.15 V
2.7 V	1.5 V	2.7 V	1.5 V	V _{OL} + 0.3 V
3.0 V to 3.6 V	1.5 V	2.7 V	1.5 V	V _{OL} + 0.3 V
4.5 V to 5.5 V	0.5 × V _{CC}	V _{CC}	0.5 × V _{CC}	V _{OL} + 0.3 V

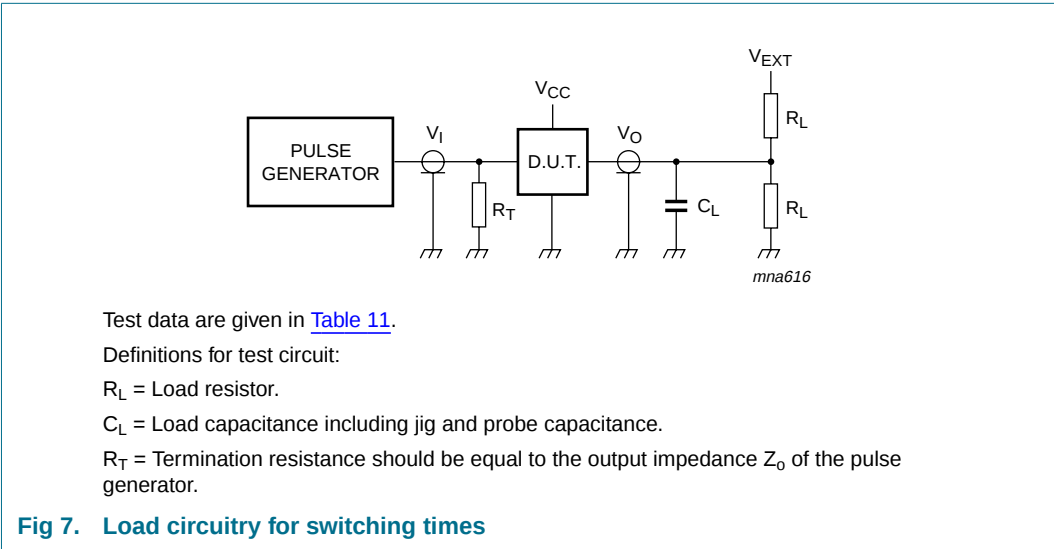


Table 11: Test data

Supply voltage	Input		Load		V _{EXT}
V _{CC}	V _I	t _r = t _f	C _L	R _L	t _{pZL} , t _{pLZ}
1.65 V to 1.95 V	V _{CC}	≤ 2.0 ns	30 pF	1 kΩ	2 × V _{CC}
2.3 V to 2.7 V	V _{CC}	≤ 2.0 ns	30 pF	500 Ω	2 × V _{CC}
2.7 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	6 V
3.0 V to 3.6 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	6 V
4.5 V to 5.5 V	V _{CC}	≤ 2.5 ns	50 pF	500 Ω	2 × V _{CC}

14. Package outline

TSSOP8: plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm SOT505-2

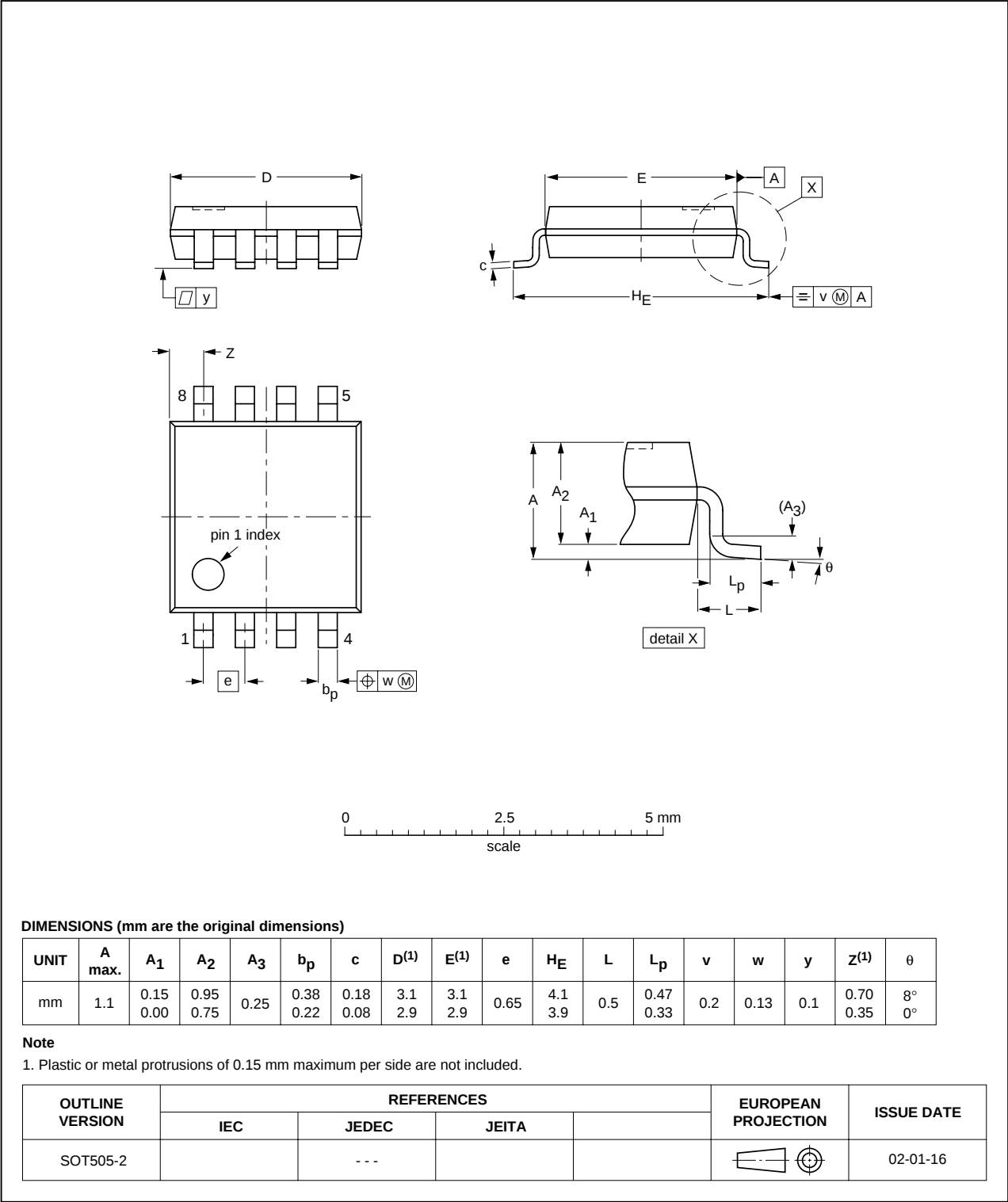


Fig 8. Package outline SOT505-2 (TSSOP8)

VSSOP8: plastic very thin shrink small outline package; 8 leads; body width 2.3 mm

SOT765-1

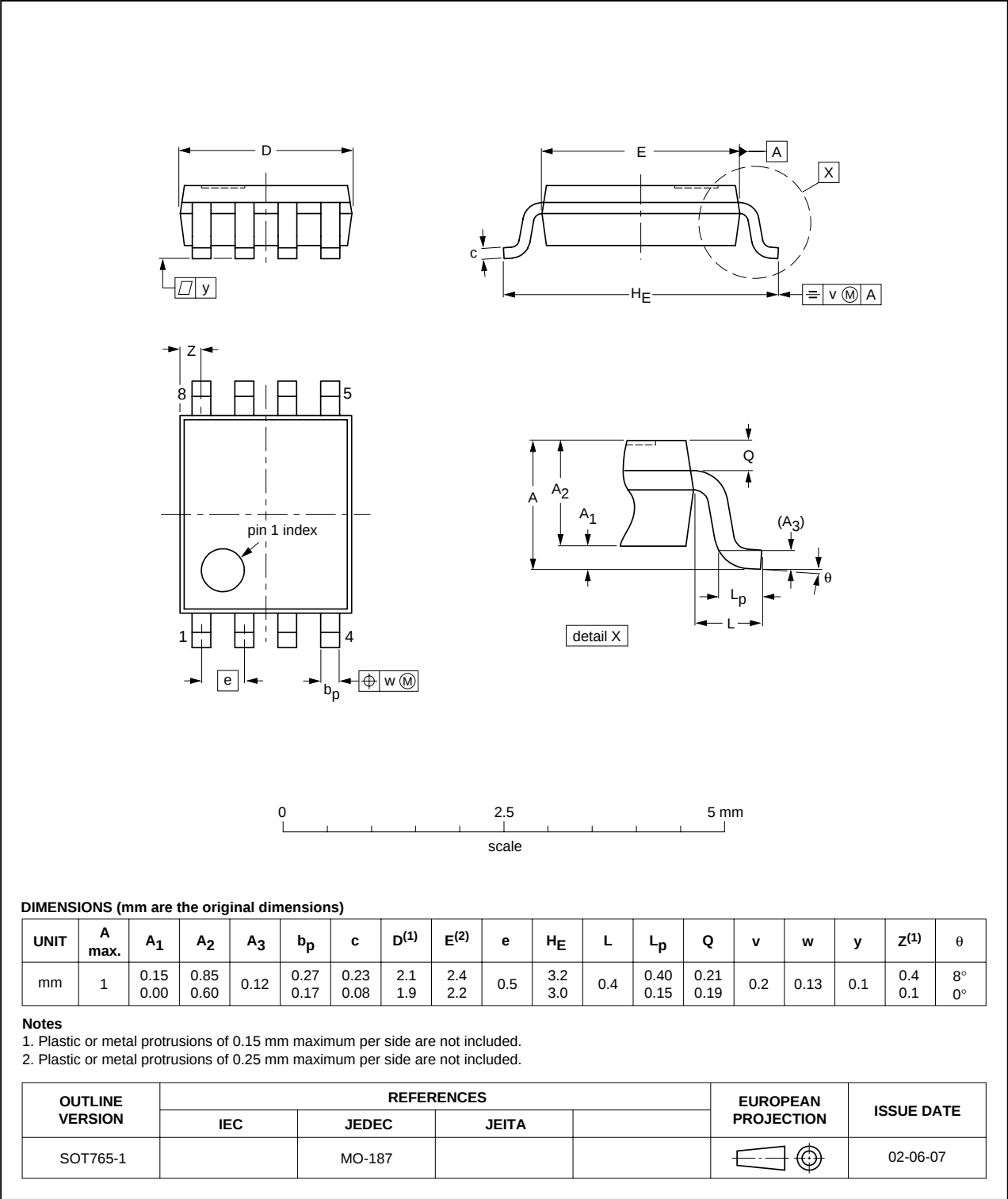
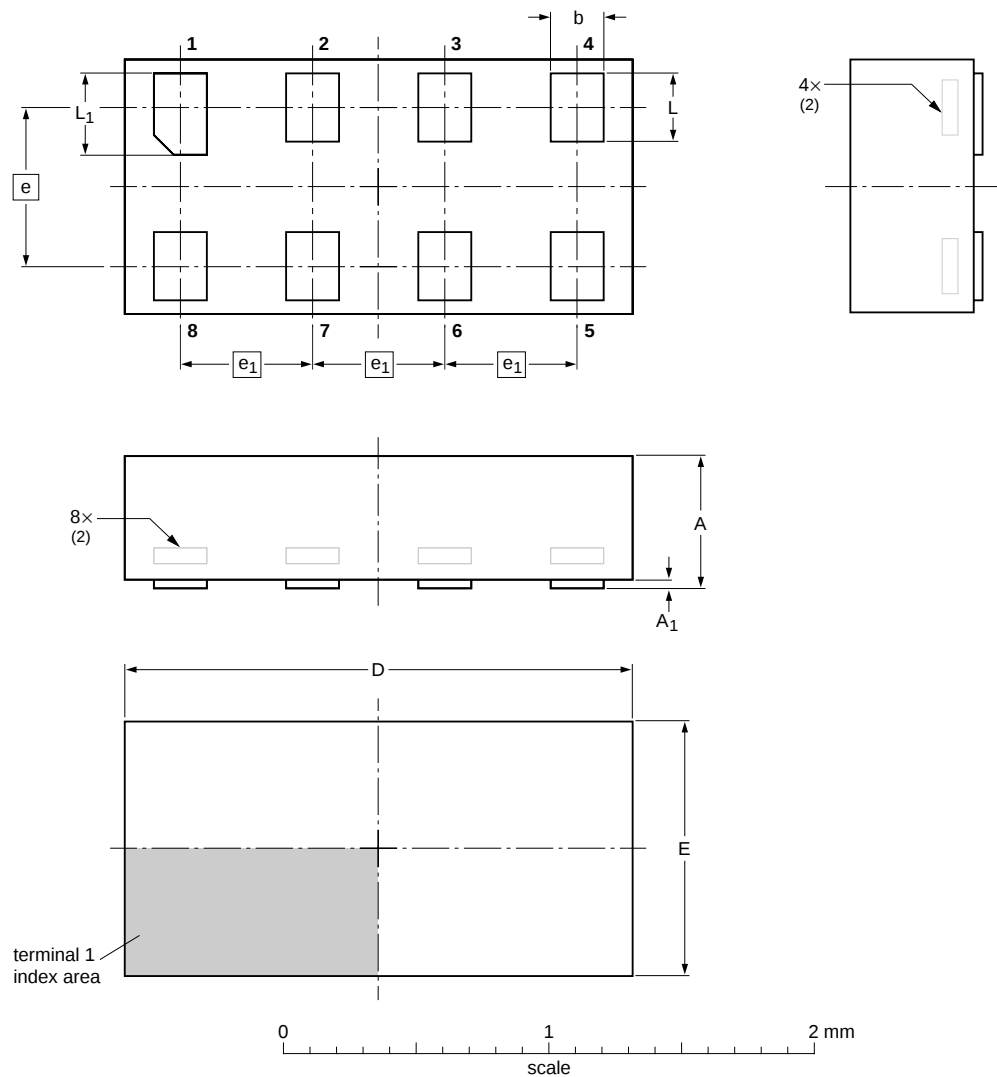


Fig 9. Package outline SOT765-1 (VSSOP8)

XSON8: plastic extremely thin small outline package; no leads; 8 terminals; body 1 x 1.95 x 0.5 mm SOT833-1



DIMENSIONS (mm are the original dimensions)

UNIT	A ⁽¹⁾ max	A ₁ max	b	D	E	e	e ₁	L	L ₁
mm	0.5	0.04	0.25 0.17	2.0 1.9	1.05 0.95	0.6	0.5	0.35 0.27	0.40 0.32

- Notes
- 1. Including plating thickness.
 - 2. Can be visible in some manufacturing processes.

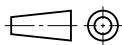
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT833-1	---	MO-252	---			04-07-22 04-11-09

Fig 10. Package outline SOT833-1 (XSON8)

15. Revision history

Table 12: Revision history

Document ID	Release date	Data sheet status	Change notice	Doc. number	Supersedes
74LVC3G07_3	20050201	Product data sheet	-	9397 750 14542	74LVC3G07_2
Modifications: Changed: type number 74LVC3G07GT (XSON8 package).					
74LVC3G07_2	20041027	Product data sheet	-	9397 750 13791	74LVC3G07_1
74LVC3G07_1	20040608	Product data sheet	-	9397 750 13267	-

16. Data sheet status

Level	Data sheet status ^[1]	Product status ^{[2] [3]}	Definition
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
II	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
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[1] Please consult the most recently issued data sheet before initiating or completing a design.

[2] The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL <http://www.semiconductors.philips.com>.

[3] For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

17. Definitions

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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